

Sergei Baranovskii

List of Publications by Year in descending order

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times ranked

3195
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#	ARTICLE	IF	CITATIONS
1	Parametrization of the Gaussian Disorder Model to Account for the High Carrier Mobility in Disordered Organic Transistors. <i>Physical Review Applied</i> , 2021, 15, .	3.8	17
2	Energy Scaling of Compositional Disorder in Ternary Transitionâ€Metal Dichalcogenide Monolayers. <i>Advanced Electronic Materials</i> , 2021, 7, 2100196.	5.1	11
3	Tunneling current modulation in atomically precise graphene nanoribbon heterojunctions. <i>Nature Communications</i> , 2021, 12, 2542.	12.8	22
4	Comment on â€Charge transport in disordered semiconducting polymers driven by nuclear tunnelingâ€. <i>Physical Review B</i> , 2020, 102, .	3.2	1
5	Percolation description of charge transport in the random barrier model applied to amorphous oxide semiconductors. <i>Europhysics Letters</i> , 2019, 127, 57004.	2.0	6
6	Percolation description of charge transport in amorphous oxide semiconductors. <i>Physical Review B</i> , 2019, 100, .	3.2	20
7	Rethinking the theoretical description of photoluminescence in compound semiconductors. <i>Journal of Applied Physics</i> , 2018, 123, 055703.	2.5	6
8	Mott Lecture: Description of Charge Transport in Disordered Organic Semiconductors: Analytical Theories and Computer Simulations. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2018, 215, 1700676.	1.8	51
9	Release of carriers from traps enhanced by hopping. <i>Physical Review B</i> , 2018, 98, .	3.2	7
10	Field-enhanced mobility in the multiple-trapping regime. <i>Physical Review B</i> , 2018, 98, .	3.2	6
11	Transport of electrons in lead oxide studied by CELIV technique. <i>Journal Physics D: Applied Physics</i> , 2017, 50, 035103.	2.8	13
12	Excitation dependence of the photoluminescence lineshape in Ga(NAsP)/GaP multiple quantum well: experiment and Monte-Carlo simulation. <i>Journal Physics D: Applied Physics</i> , 2017, 50, 025105.	2.8	2
13	STEMsalabim: A high-performance computing cluster friendly code for scanning transmission electron microscopy image simulations of thin specimens. <i>Ultramicroscopy</i> , 2017, 177, 91-96.	1.9	50
14	Analytical theory for charge carrier recombination in blend organic solar cells. <i>Physical Review B</i> , 2017, 95, .	3.2	6
15	Fundamental characteristic length scale for the field dependence of hopping charge transport in disordered organic semiconductors. <i>Physical Review B</i> , 2017, 96, .	3.2	25
16	Field dependence of hopping mobility: Lattice models against spatial disorder. <i>Physical Review B</i> , 2017, 96, .	3.2	18
17	Charge Transport in Disordered Materials. <i>Springer Handbooks</i> , 2017, , 1-1.	0.6	7
18	Electron spin flip Raman spectroscopy of the diluted magnetic semiconductor Zn_{1-x}Mn_xSe below the metalâ€insulator transition. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016, 13, 542-545.	0.8	0

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19	Columnar recombination for X-ray generated electron-holes in amorphous selenium and its significance in a-Se x-ray detectors. <i>Journal of Applied Physics</i> , 2016, 119, .	2.5	19
20	Why the apparent order of bimolecular recombination in blend organic solar cells can be larger than two: A topological consideration. <i>Applied Physics Letters</i> , 2016, 109, 033301.	3.3	12
21	Disorder-induced absorption of far-infrared waves by acoustic modes in nematic liquid crystals. <i>Journal of Applied Physics</i> , 2016, 120, 074901.	2.5	0
22	Influence of growth temperature and disorder on spectral and temporal properties of Ga(NAsP) heterostructures. <i>Journal of Applied Physics</i> , 2016, 119, .	2.5	7
23	Pyramidal Structure Formation at the Interface between III/V Semiconductors and Silicon. <i>Chemistry of Materials</i> , 2016, 28, 3265-3275.	6.7	37
24	Band edge smearing due to compositional disorder in multi-component d -dimensional alloys. <i>Physica Status Solidi - Rapid Research Letters</i> , 2016, 10, 911-914.	2.4	3
25	Charge transport mechanism in lead oxide revealed by CELIV technique. <i>Scientific Reports</i> , 2016, 6, 33359.	3.3	21
26	Compositional dependence of the band gap in Ga(NAsP) quantum well heterostructures. <i>Journal of Applied Physics</i> , 2015, 118, .	2.5	8
27	Two-energy-scale model for description of the thermal quenching of photoluminescence in disordered Ga(As,Bi). <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015, 12, 1187-1190.	0.8	2
28	Energy scale of compositional disorder in Ga(AsBi). <i>Journal Physics D: Applied Physics</i> , 2015, 48, 425101.	2.8	7
29	Thermal quenching of photoluminescence in Ga(AsBi). <i>Journal of Applied Physics</i> , 2015, 117, 025709.	2.5	19
30	Theoretical tools for the description of charge transport in disordered organic semiconductors. <i>Journal of Physics Condensed Matter</i> , 2015, 27, 093201.	1.8	54
31	Theory to carrier recombination in organic disordered semiconductors. <i>Journal of Applied Physics</i> , 2014, 115, 223713.	2.5	11
32	Large positive magnetoresistance effects in the dilute magnetic semiconductor (Zn,Mn)Se in the regime of electron hopping. <i>Journal of Applied Physics</i> , 2014, 116, 083710.	2.5	12
33	Theoretical description of charge transport in disordered organic semiconductors. <i>Physica Status Solidi (B): Basic Research</i> , 2014, 251, 487-525.	1.5	273
34	Structural characteristics of gallium metal deposited on Si (001) by MOCVD. <i>Journal of Crystal Growth</i> , 2014, 405, 102-109.	1.5	30
35	Energy position of the transport path in disordered organic semiconductors. <i>Journal of Physics Condensed Matter</i> , 2014, 26, 255801.	1.8	15
36	Nonexponential photoluminescence transients in a Ga(NAsP) lattice matched to a (001) silicon substrate. <i>Physical Review B</i> , 2013, 87, .	3.2	13

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37	Advanced percolation solution for hopping conductivity. <i>Physical Review B</i> , 2013, 87, .	3.2	29
38	Scaling approach to hopping magnetoresistivity in dilute magnetic semiconductors. <i>Physical Review B</i> , 2013, 88, .	3.2	7
39	Non-Onsager mechanism of long-wave photogeneration in amorphous selenium at high electric fields. <i>Applied Physics Letters</i> , 2012, 100, .	3.3	10
40	Compositional disorder anomalies in Ga(N,P,As)/GaP quantum well structures. <i>Journal of Physics: Conference Series</i> , 2012, 376, 012021.	0.4	0
41	Energy scaling of compositional disorder in Ga(N,P,As)/GaP quantum well structures. <i>Physical Review B</i> , 2012, 86, .	3.2	16
42	Calculating the Efficiency of Exciton Dissociation at the Interface between a Conjugated Polymer and an Electron Acceptor. <i>Journal of Physical Chemistry Letters</i> , 2012, 3, 1214-1221.	4.6	95
43	How to Find Out the Density of States in Disordered Organic Semiconductors. <i>Physical Review Letters</i> , 2012, 108, 226403.	7.8	87
44	Theory of exciton dissociation at the interface between a conjugated polymer and an electron acceptor. <i>Physical Review B</i> , 2011, 84, .	3.2	62
45	On the efficiency of exciton dissociation at the interface between a conjugated polymer and an electron acceptor. <i>Applied Physics Letters</i> , 2011, 99, .	3.3	37
46	Negative differential conductivity in the hopping transport model. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010, 207, 613-616.	1.8	1
47	Effect of electric field on diffusion in disordered materials. II. Two- and three-dimensional hopping transport. <i>Physical Review B</i> , 2010, 81, .	3.2	39
48	Concentration dependence of the transport energy level for charge carriers in organic semiconductors. <i>Applied Physics Letters</i> , 2010, 97, 143302.	3.3	30
49	Role of diffusion in two-dimensional bimolecular recombination. <i>Applied Physics Letters</i> , 2010, 96, 213304.	3.3	15
50	Peculiarities of the photoluminescence of metastable Ga(N,As,P)/GaP quantum well structures. <i>Physical Review B</i> , 2010, 82, .	3.2	40
51	Effect of electric field on diffusion in disordered materials. I. One-dimensional hopping transport. <i>Physical Review B</i> , 2010, 81, .	3.2	31
52	Influence of disorder on electrically and optically detected electron spin nutation. <i>Physical Review B</i> , 2009, 79, .	3.2	10
53	Reversible vs irreversible photodarkening in a-Se: the kinetics study. <i>Journal of Materials Science: Materials in Electronics</i> , 2009, 20, 111-115.	2.2	8
54	Lucky-drift model for impact ionization in amorphous semiconductors. <i>Journal of Materials Science: Materials in Electronics</i> , 2009, 20, 221-225.	2.2	29

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55	Description of Charge Transport in Disordered Organic Materials. <i>Advances in Polymer Science</i> , 2009, , 1-28.	0.8	4
56	Formation Energies of Antiphase Boundaries in GaAs and GaP: An ab Initio Study. <i>International Journal of Molecular Sciences</i> , 2009, 10, 5104-5114.	4.1	45
57	Fluctuations of the peak current of tunnel diodes in multi-junction solar cells. <i>Journal Physics D: Applied Physics</i> , 2009, 42, 155101.	2.8	13
58	One-dimensional lucky-drift model with scattering and movement asymmetries for impact ionization in amorphous semiconductors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 796-799.	0.8	4
59	Effective temperature for hopping transport in a Gaussian DOS. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 722-724.	0.8	12
60	Simulation of the Coulomb gap evolution in the Coulomb glass. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 694-698.	0.8	3
61	The influence of the water surrounding on a long-distance electron transport in the DNA. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 714-717.	0.8	0
62	Influence of non-random incorporation of Mn ions on the magnetotransport properties of Ga _x Mn _x As alloys. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 819-823.	0.8	1
63	Hopping energy relaxation of localized excitons in GaP(N). <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 768-771.	0.8	3
64	Photoconductivity in amorphous selenium blocking structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008, 5, 790-795.	0.8	12
65	On the application of the Edwards-Anderson order parameter to the Coulomb glass. <i>Physica Status Solidi (B): Basic Research</i> , 2008, 245, 481-484.	1.5	1
66	Effect of exchange coupling on coherently controlled spin-dependent transition rates. <i>Physical Review B</i> , 2008, 77, .	3.2	29
67	Avalanche multiplication in amorphous selenium and its utilization in imaging. <i>Journal of Non-Crystalline Solids</i> , 2008, 354, 2691-2696.	3.1	32
68	Analytical theory for favorable defects in tunnel diodes. <i>Journal of Applied Physics</i> , 2008, 104, .	2.5	3
69	Spectral and time dependences of the energy transfer of bound optical excitations in GaP(N). <i>Journal of Physics Condensed Matter</i> , 2008, 20, 015217.	1.8	15
70	Resonant tunneling as a dominant transport mechanism in n-GaAs ⁺ p-GaAs tunnel diodes. <i>Applied Physics Letters</i> , 2008, 92, 243504.	3.3	3
71	Similarities in the kinetics of photocrystallization and photodarkening in a-Se. <i>Applied Physics Letters</i> , 2008, 93, .	3.3	10
72	Resonant electron tunneling through defects in GaAs tunnel diodes. <i>Journal of Applied Physics</i> , 2008, 104, 094506.	2.5	22

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73	Tailoring the magnetoresistance of MnAs ^δ /GaAs:Mn granular hybrid nanostructures. Applied Physics Letters, 2008, 92, 223119.	3.3	29
74	Effective temperature for hopping transport in a Gaussian density of states. Physical Review B, 2008, 77, .	3.2	37
75	Exact Solution for Hopping Dissociation of Geminate Electron-Hole Pairs in a Disordered Chain. Physical Review Letters, 2008, 100, 196602.	7.8	71
76	Hopping conduction in strong electric fields: Negative differential conductivity. Physical Review B, 2008, 78, .	3.2	18
77	Quantitative modeling of the annealing-induced changes of the magnetotransport in Ga _{1-x} Mn _x As alloys. Journal of Applied Physics, 2007, 102, 073712.	2.5	7
78	Spectral dependence of the photoluminescence decay in disordered semiconductors. Applied Physics Letters, 2007, 91, 021903.	3.3	26
79	Avalanche multiplication phenomenon in amorphous semiconductors: Amorphous selenium versus hydrogenated amorphous silicon. Journal of Applied Physics, 2007, 102, .	2.5	52
80	Relaxation and recombination in InAs quantum dots. Physica Status Solidi (B): Basic Research, 2007, 244, 2803-2815.	1.5	10
81	Charge Transport in Disordered Materials. , 2006, , 161-186.		7
82	Kinetics of the photostructural changes in a-Se films. Journal of Applied Physics, 2006, 100, 113506.	2.5	20
83	Strong non-Arrhenius temperature dependence of the resistivity in the regime of traditional band transport. Applied Physics Letters, 2006, 89, 112116.	3.3	26
84	On the concentration and field dependences of the hopping mobility in disordered organic solids. Journal of Non-Crystalline Solids, 2006, 352, 1644-1647.	3.1	11
85	Simulation of the phononless hopping in a Coulomb glass. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 279-282.	0.8	1
86	Non-radiative recombination of optical excitations in (GaIn)(NAs) quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2481-2484.	0.8	2
87	Nature and dynamics of carrier escape from InAs/GaAs quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2397-2401.	0.8	10
88	Magnetic Interactions in Granular Paramagnetic/Ferromagnetic GaAs: Mn/MnAs Hybrids. Journal of Superconductivity and Novel Magnetism, 2006, 18, 315-320.	0.5	23
89	Model of temperature quenching of photoluminescence in disordered semiconductors and comparison to experiment. Physical Review B, 2006, 73, .	3.2	65
90	Model of annealing-induced short-range order effects in (GaIn)(NP) alloys. Physical Review B, 2006, 74, .	3.2	8

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91	Nanoanalytical quantification of the nitrogen content in Ga(NAs) δ -GaAs by using transmission electron microscopy in combination with refined structure factor calculation. Applied Physics Letters, 2006, 88, 081910.	3.3	11
92	Transport and recombination through weakly coupled localized spin pairs in semiconductors during coherent spin excitation. Physical Review B, 2006, 74, .	3.2	27
93	Spin-dependent localization effects in GaAs:Mn/MnAs granular paramagnetic δ -ferromagnetic hybrids at low temperatures. Superlattices and Microstructures, 2005, 37, 321-326.	3.1	20
94	Theoretical description of hopping transport in disordered materials. Thin Solid Films, 2005, 487, 2-7.	1.8	32
95	Quantitative description of disorder parameters in (GaIn)(NAs) quantum wells from the temperature-dependent photoluminescence spectroscopy. Journal of Applied Physics, 2005, 98, 063518.	2.5	81
96	Temperature-dependent optical properties of InAs δ -GaAs quantum dots: Independent carrier versus exciton relaxation. Physical Review B, 2005, 72, .	3.2	53
97	Effects of dynamic disorder on the charge transport via DNA molecules. Physical Chemistry Chemical Physics, 2005, 7, 1514.	2.8	7
98	Quantitative interpretation of the phonon-assisted redistribution processes of excitons in Zn $_{1-x}$ Cd $_x$ Se quantum islands. Physical Review B, 2004, 69, .	3.2	28
99	Concentration dependence of the hopping mobility in disordered organic solids. Physical Review B, 2004, 69, .	3.2	78
100	Influence of magnetic-field-induced tuning of disorder and band structure on the magnetoresistance of paramagnetic dilute magnetic semiconductors. Physical Review B, 2004, 69, .	3.2	21
101	Hopping transport in 1D chains (DNA vs. DLC). Physica Status Solidi (B): Basic Research, 2004, 241, 76-82.	1.5	10
102	Base sequence dependence of charge transport via short DNA bridges. Physica Status Solidi (B): Basic Research, 2004, 241, R46-R48.	1.5	2
103	Hopping relaxation of excitons in GaInNAs/GaNAs quantum wells. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 109-112.	0.8	43
104	Potential fluctuations in disordered semiconductors measured by transport and optical methods. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 113-116.	0.8	2
105	Concentration dependence of the hopping mobility in disordered organic solids. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 168-171.	0.8	2
106	Lucky-drift model for avalanche multiplication in amorphous semiconductors. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 1186-1193.	0.8	24
107	Columnar [001]-oriented nitrogen order in Ga(NAs) and (GaIn)(NAs) alloys. Applied Physics Letters, 2004, 85, 5908-5910.	3.3	34
108	Lucky drift impact ionization in amorphous semiconductors. Journal of Applied Physics, 2004, 96, 2037-2048.	2.5	70

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109	On the light absorption in amorphous semiconductors. Journal of Materials Science: Materials in Electronics, 2003, 14, 707-710.	2.2	1
110	Temperature dependent excitonic relaxation in CdSe/ZnSe quantum islands: experiment and computer simulation. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 1509-1513.	0.8	3
111	Percolation Approach to Hopping Transport in Organic Disordered Solids. Physica Status Solidi (B): Basic Research, 2002, 230, 281-288.	1.5	64
112	One-dimensional hopping transport in disordered organic solids. Analytic calculations. Physical Review B, 2001, 63, .	3.2	67
113	One-dimensional hopping transport in disordered organic solids. II. Monte Carlo simulations. Physical Review B, 2001, 63, .	3.2	36
114	On disorder-enhanced diffusion in condensed aromatic melts. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 2001, 81, 955-964.	0.6	7
115	Energy relaxation of localized excitons at finite temperature. Semiconductor Science and Technology, 2001, 16, 486-492.	2.0	38
116	Fluctuation-stimulated variable-range hopping. Solid State Communications, 2000, 113, 587-591.	1.9	28
117	Charge-carrier transport in disordered organic solids. Physical Review B, 2000, 62, 7934-7938.	3.2	144
118	Light-induced nucleation and optical absorption in cesium vapor. Journal of Chemical Physics, 2000, 113, 4171-4178.	3.0	7
119	Hopping conductivity in gated δ -doped GaAs: universality of prefactor. Solid State Communications, 1999, 112, 21-24.	1.9	15
120	On the conduction mechanism in ionic glasses. Journal of Chemical Physics, 1999, 111, 7546-7557.	3.0	113
121	Transport properties of microcrystalline silicon at low temperatures. Semiconductors, 1998, 32, 807-811.	0.5	8
122	On the Transport Properties of Microcrystalline Silicon at Low Temperatures. Physica Status Solidi (B): Basic Research, 1998, 205, 147-150.	1.5	18
123	On the Einstein Relation for Hopping Electrons. Physica Status Solidi (B): Basic Research, 1998, 205, 87-90.	1.5	24
124	Thermally Stimulated Conductivity in Disordered Semiconductors at Low Temperatures. Physica Status Solidi (B): Basic Research, 1998, 205, 91-96.	1.5	2
125	Temperature-Dependent Exciton Luminescence in Coupled Quantum Wells. Physica Status Solidi (B): Basic Research, 1998, 205, R19-R20.	1.5	8
126	Photoinduced nucleation in supersaturated mercury vapor. Journal of Chemical Physics, 1998, 108, 9775-9782.	3.0	15

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127	Temperature-dependent exciton luminescence in quantum wells by computer simulation. <i>Physical Review B</i> , 1998, 58, 13081-13087.	3.2	134
128	Comment on "Absence of Carrier Hopping in Porous Silicon". <i>Physical Review Letters</i> , 1998, 81, 3804-3804.	7.8	2
129	Role of interactions in the energy-loss hopping and recombination of two-dimensional electrons and holes. <i>Physical Review B</i> , 1997, 55, 4575-4579.	3.2	5
130	Evidence for Dipole-Dipole Hopping of GaAs Quantum Well Excitons. <i>Physical Review Letters</i> , 1997, 78, 4261-4264.	7.8	16
131	Thermally stimulated conductivity in disordered semiconductors at low temperatures. <i>Physical Review B</i> , 1997, 55, 16226-16232.	3.2	17
132	The applicability of the transport-energy concept to various disordered materials. <i>Journal of Physics Condensed Matter</i> , 1997, 9, 2699-2706.	1.8	85
133	Long-time behavior of the diffusion-controlled $A+B^{\dagger}O$ reaction with hopping energy relaxation. <i>Journal of Chemical Physics</i> , 1997, 106, 3157-3158.	3.0	0
134	Photoconductivity response time in amorphous semiconductors. <i>Physical Review B</i> , 1995, 51, 9661-9667.	3.2	44
135	High-field hopping transport in band tails of disordered semiconductors. <i>Physical Review B</i> , 1995, 51, 16705-16713.	3.2	60
136	Tunneling conduction in Co-cluster/tetraoctylammonium bromide/poly(phenylacetylene/phenylenevinylene) nanocomposites. <i>Journal of Applied Physics</i> , 1995, 78, 7130-7136.	2.5	19
137	Temperature-Induced Smearing of the Coulomb Gap: Experiment and Computer Simulation. <i>Physical Review Letters</i> , 1995, 75, 4764-4767.	7.8	35
138	The concept of transport energy and its application to steady-state photoconductivity in amorphous silicon. <i>Journal of Non-Crystalline Solids</i> , 1995, 190, 283-287.	3.1	47
139	On the time decay of the photoinduced condensation in supersaturated vapors. <i>Journal of Chemical Physics</i> , 1995, 103, 7796-7800.	3.0	5
140	Photoconductivity of Doped Amorphous Semiconductors at Low Temperatures. <i>Molecular Crystals and Liquid Crystals</i> , 1994, 252, 23-30.	0.3	0
141	Recombination of Alloy-Trapped Excitons in Ternary Solid Solutions with Common Cation Components. <i>Physica Status Solidi (B): Basic Research</i> , 1994, 184, 159-170.	1.5	16
142	Dynamics of localized excitons and high-excitations effects in $\text{In}_{1-x}\text{Ga}_x$ quantum wells and heterostructures. <i>Physica B: Condensed Matter</i> , 1993, 191, 90-101.	2.7	31
143	Exciton line broadening by compositional disorder in alloy quantum wells. <i>Physical Review B</i> , 1993, 48, 17149-17154.	3.2	32
144	Electron drift mobility in hydrogenated amorphous $\text{Si}_{1-x}\text{C}_x$ with a low carbon content. <i>Philosophical Magazine Letters</i> , 1993, 68, 173-178.	1.2	11

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145	Monte-Carlo Simulation of Energy Relaxation of Interacting Carriers in a-Si:H Under Arbitrary Electric Fields. Materials Research Society Symposia Proceedings, 1993, 297, 467.	0.1	0
146	Electron glass transition in a lightly doped semiconductor. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1992, 65, 685-693.	0.6	9
147	Optical dephasing in semiconductor mixed crystals. Physical Review B, 1992, 46, 4564-4581.	3.2	62
148	Comment on "Phase transition of an exciton system in GaAs coupled quantum wells" and on "Fermi-Dirac distribution of excitons in coupled quantum wells". Physical Review Letters, 1992, 69, 993-993.	7.8	12
149	Temperature dependence of the linewidth of shallow impurity spectral lines in lightly doped weakly compensated semiconductors. Journal of Applied Physics, 1992, 71, 2452-2454.	2.5	1
150	Optical- and acoustical-phonon-assisted hopping of localized excitons in CdTe/ZnTe quantum wells. Physical Review B, 1992, 45, 4253-4257.	3.2	58
151	Dimensional quantization in a-Si:H quantum-well structures: The alloy model. Physical Review B, 1990, 41, 7701-7704.	3.2	34
152	HOPPING PHOTOCONDUCTIVITY IN AMORPHOUS SEMICONDUCTORS: DEPENDENCE ON TEMPERATURE, ELECTRIC FIELD AND FREQUENCY. , 1990, , 161-191.		38
153	Electronic transport and recombination in amorphous semiconductors at low temperatures. Physical Review Letters, 1989, 62, 2989-2992.	7.8	140
154	Coulomb gap in disordered systems: computer simulation. Journal of Physics C: Solid State Physics, 1979, 12, 1023-1034.	1.5	150
155	Comment on "Interplay of Structural and Optoelectronic Properties in Formamidinium Mixed Tin-Lead Triiodide Perovskites". Advanced Functional Materials, 0, , 2201309.	14.9	2